

# **Description**

The HXY8205LI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



#### **General Features**

 $V_{DS} = 20V, I_{D} = 6A$ 

 $R_{DS(ON)}$  <25m $\Omega$  @  $V_{GS}$ =4.5V

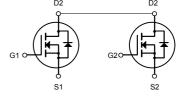
### SOT23-6L

### **Application**

Battery protection

Load switch

Power management



**Dual N-Channel MOSFET** 

# **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
HXY8205LI	SOT23-6L	8205 XXX YYYY	3000

## Absolute Maximum Ratings@T<sub>i</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>GS</sub>	Gate-Source Voltage	<u>+</u> 10	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Drain Current, V <sub>GS</sub> @ 4.5V <sup>3</sup>	6	Α
Іт	Pulsed Drain Current <sup>1</sup>	25	Α
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation	1.25	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	100	°C/W



## Electrical Characteristics (T<sub>A</sub>=25℃ unless otherwise noted)

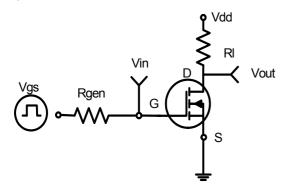
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20	21	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =19.5V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.5	0.7	1.2	V
Danier Courses On Otata Basistana	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	-	22	25	mΩ
Drain-Source On-State Resistance		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3A	-	26	31	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =4A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>		-	600	-	PF
Output Capacitance	Coss	$V_{DS}$ =8 $V$ , $V_{GS}$ =0 $V$ , F=1.0MHz	-	330	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVITIZ	-	140	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	18	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =10 $V$ , $I_{D}$ =1 $A$	-	5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =4 $V$ , $R_{GEN}$ =10 $\Omega$	-	43	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	20	-	nS
Total Gate Charge	Qg	\/ 40\/  44	-	11	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=10V,I_{D}=4A,$	-	2.3	-	nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =4.5V	-	2.5	-	nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =2A	-	0.8	1.2	V
Diode Forward Current (Note 2)	Is		-	-	2	Α

#### Notes:

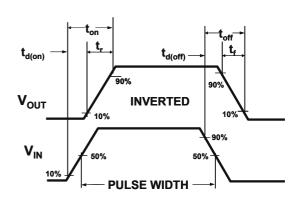
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



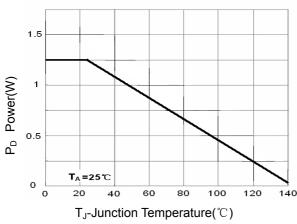
#### **Typical Electrical and Thermal Characteristics**



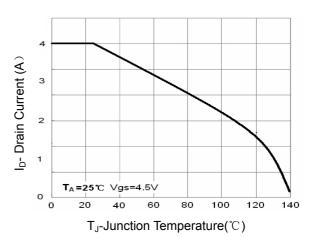
**Figure 1:Switching Test Circuit** 



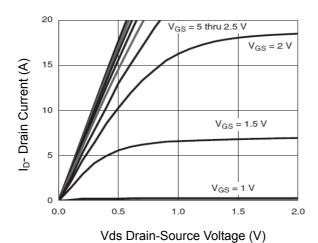
**Figure 2:Switching Waveforms** 



**Figure 3 Power Dissipation** 



**Figure 4 Drain Current** 



**Figure 5 Output Characteristics** 

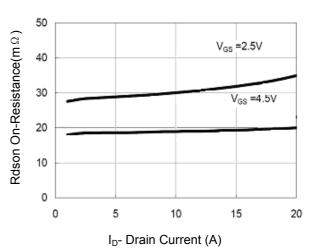
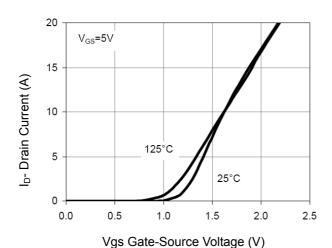


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 

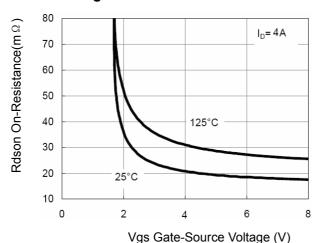
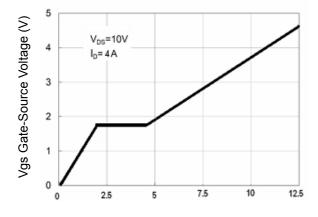
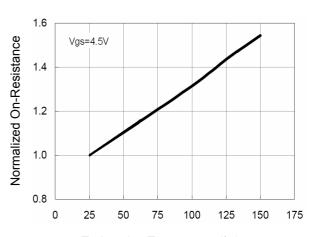


Figure 9 Rdson vs Vgs



Qg Gate Charge (nC) Figure 11 Gate Charge



T<sub>J</sub>-Junction Temperature(°C)

Figure 8 Drain-Source On-Resistance

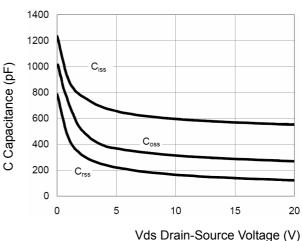
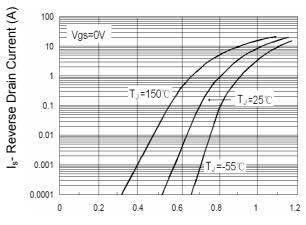


Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward



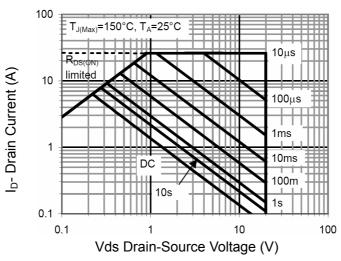
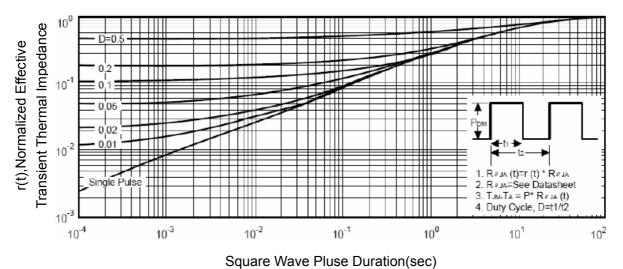
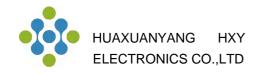


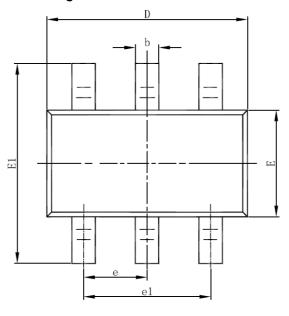
Figure 13 Safe Operation Area

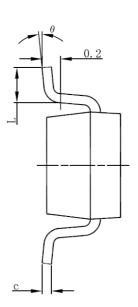


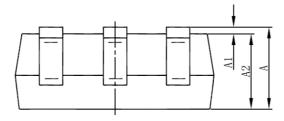
**Figure 14 Normalized Maximum Transient Thermal Impedance** 



### **SOT23-6L Package Information**







C. mla a l	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950(BSC)		0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

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